1.1 nV/√Hz Noise, Low Power, Precision Operational Amplifier

FEATURES

- Low Voltage Noise: 1.1 nV/√Hz at 1 kHz
- Input Voltage Noise:
  80 nVpp (0.1 Hz to 10 Hz)
- THD+N: –136dB (G = 1, f = 1 kHz)
- Offset Voltage: 350 μV (max)
- Offset Voltage Drift: 0.35 μV/°C (typ)
- Low Supply Current: 6 mA/Ch (max)
- Unity-Gain Stable
- Gain Bandwidth Product:
  80 MHz (G = 100)
  45 MHz (G = 1)
- Slew Rate: 27 V/μs
- 16-Bit Settling: 700 ns
- Wide Supply Range:
  ±2.25 V to ±18 V, 4.5 V to 36 V
- Rail-to-rail output
- Output current: 30 mA

APPLICATIONS

- Down-Hole Drilling
- High Temperature Environments

SUPPORTS EXTREME TEMPERATURE APPLICATIONS

- Controlled Baseline
- One Assembly/Test Site
- One Fabrication Site
- Available in Extreme (–55°C/150°C) Temperature Range (1)
- Extended Product Life Cycle
- Extended Product-Change Notification
- Product Traceability
- Texas Instruments high temperature products utilize highly optimized silicon (die) solutions with design and process enhancements to maximize performance over extended temperatures.

DESCRIPTION

The OPA2211 is a precision operational amplifier that achieves very low 1.1 nV/√Hz noise density with a supply current of only 3.6 mA. This device also offers rail-to-rail output swing, which maximizes dynamic range.

The extremely low voltage and low current noise, high speed, and wide output swing of the OPA2211 make this device an excellent choice as a loop filter amplifier in PLL applications.

In precision data acquisition applications, the OPA2211 provides 700-ns settling time to 16-bit accuracy throughout 10-V output swings. This ac performance, combined with only 240-μV of offset and 0.35-μV/°C of drift over temperature, makes the OPA2211 ideal for driving high-precision 16-bit analog-to-digital converters (ADCs) or buffering the output of high-resolution digital-to-analog converters (DACs).

The OPA2211 is specified over a wide dual-power supply range of ±2.25 V to ±18 V, or for single-supply operation from 4.5 V to 36 V.

This op amp is specified from T_J = –55°C to 150°C.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet. All trademarks are the property of their respective owners.
**Table 1. ORDERING INFORMATION**

<table>
<thead>
<tr>
<th>$T_J$</th>
<th>PACKAGE</th>
<th>ORDERABLE PART NUMBER</th>
<th>TOP-SIDE MARKING</th>
</tr>
</thead>
<tbody>
<tr>
<td>–55°C to 150°C</td>
<td>PWP</td>
<td>OPA2211SPWP</td>
<td>OP2211S</td>
</tr>
</tbody>
</table>

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

**ABSOLUTE MAXIMUM RATINGS**

Over operating free-air temperature range (unless otherwise noted).

<table>
<thead>
<tr>
<th></th>
<th>VALUE</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>Supply Voltage</td>
<td>$V_S = (V+) - (V–)$</td>
<td>40 V</td>
</tr>
<tr>
<td>Input Voltage</td>
<td>$(V–) - 0.5$ to $(V+) + 0.5$</td>
<td>V</td>
</tr>
<tr>
<td>Input Current (Any pin except power-supply pins)</td>
<td>±10 mA</td>
<td></td>
</tr>
<tr>
<td>Output Short-Circuit$^{(2)}$</td>
<td>Continuous</td>
<td></td>
</tr>
<tr>
<td>Storage Temperature, ($T_S$)</td>
<td>–65 to +165 °C</td>
<td></td>
</tr>
<tr>
<td>Junction Temperature, ($T_J$)</td>
<td>–55 to +165 °C</td>
<td></td>
</tr>
<tr>
<td>ESD Ratings</td>
<td>Human Body Model (HBM)</td>
<td>3000 V</td>
</tr>
<tr>
<td></td>
<td>Charged Device Model (CDM)</td>
<td>1000 V</td>
</tr>
</tbody>
</table>

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not supported.

(2) Short-circuit to $V_S/2$ (ground in symmetrical dual supply setups), one amplifier per package.
# THERMAL INFORMATION

<table>
<thead>
<tr>
<th>THERMAL METRIC⁽¹⁾</th>
<th>OPA2211-HT PWP</th>
<th>UNITS</th>
</tr>
</thead>
<tbody>
<tr>
<td>θJA</td>
<td>41.2</td>
<td>°C/W</td>
</tr>
<tr>
<td>θJCtop</td>
<td>21.4</td>
<td></td>
</tr>
<tr>
<td>θJB</td>
<td>23.9</td>
<td></td>
</tr>
<tr>
<td>ΨJT</td>
<td>1.1</td>
<td></td>
</tr>
<tr>
<td>ΨJB</td>
<td>23.7</td>
<td></td>
</tr>
<tr>
<td>θJCbot</td>
<td>1.1</td>
<td></td>
</tr>
</tbody>
</table>

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

(2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.

(3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.

(5) The junction-to-top characterization parameter, ΨJT, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θJA, using a procedure described in JESD51-2a (sections 6 and 7).

(6) The junction-to-board characterization parameter, ΨJB, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θJA, using a procedure described in JESD51-2a (sections 6 and 7).

(7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
PIN CONFIGURATION

PWP PACKAGE (TOP VIEW)

OUTA 20 NC
NC 19 NC
NC 18 NC
-INA 17 V+
NC 16 NC
NC 15 NC
+INA 14 OUTB
NC 13 NC
V- 12 NC
NC 11 -INB
NC 10 -INB
## ELECTRICAL CHARACTERISTICS: $V_S = \pm 2.25V$ to $\pm 18V$

**BOLDFACE limits apply over the specified temperature range, $T_J = –55°C$ to $+150°C$.**

At $T_J = +25°C$, $R_L = 10kΩ$ connected to midsupply, $V_{CM} = V_{OUT} = $ midsupply, unless otherwise noted.

### Offset Voltage

<table>
<thead>
<tr>
<th>PARAMETER</th>
<th>CONDITIONS</th>
<th>MIN</th>
<th>TYP</th>
<th>MAX</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>Input Offset Voltage</td>
<td>$V_S = \pm 15V$</td>
<td>$\pm 50$</td>
<td>$\pm 175$</td>
<td>μV</td>
<td></td>
</tr>
<tr>
<td>Over Temperature</td>
<td>$V_S = \pm 18V$</td>
<td>$\pm 350$</td>
<td>μV</td>
<td></td>
<td></td>
</tr>
<tr>
<td>drift vs Power Supply</td>
<td>$dV_{OS}/dT$</td>
<td>0.35</td>
<td>μV/°C</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

### Input Bias Current

<table>
<thead>
<tr>
<th>PARAMETER</th>
<th>CONDITIONS</th>
<th>MIN</th>
<th>TYP</th>
<th>MAX</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>Input Bias Current</td>
<td>$V_{CM} = 0V$</td>
<td>$\pm 60$</td>
<td>$\pm 215$</td>
<td>nA</td>
<td></td>
</tr>
<tr>
<td>Over Temperature</td>
<td>$V_S = \pm 18V$</td>
<td>$\pm 350$</td>
<td>nA</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Offset Current</td>
<td>$V_{CM} = 0V$</td>
<td>$\pm 25$</td>
<td>$\pm 120$</td>
<td>nA</td>
<td></td>
</tr>
<tr>
<td>Over Temperature</td>
<td>$V_S = \pm 18V$</td>
<td>$\pm 200$</td>
<td>nA</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

### Noise

<table>
<thead>
<tr>
<th>PARAMETER</th>
<th>CONDITIONS</th>
<th>MIN</th>
<th>TYP</th>
<th>MAX</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>Input Voltage Noise</td>
<td>$f = 0.1Hz$ to $10Hz$</td>
<td>80</td>
<td>nV/√Hz</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Input Voltage Noise Density</td>
<td>$f = 10Hz$</td>
<td>2</td>
<td>nV/√Hz</td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>$f = 100Hz$</td>
<td>1.4</td>
<td>nV/√Hz</td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>$f = 1kHz$</td>
<td>1.1</td>
<td>nV/√Hz</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Input Current Noise Density</td>
<td>$f = 10Hz$</td>
<td>3.2</td>
<td>pA/√Hz</td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>$f = 1kHz$</td>
<td>1.7</td>
<td>pA/√Hz</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

### Input Voltage Range

<table>
<thead>
<tr>
<th>COMMON-MODE VOLTAGE RANGE</th>
<th>$V_S = \pm 15V$</th>
<th>(V–) + 1.8</th>
<th>(V+) – 1.4</th>
<th>V</th>
</tr>
</thead>
<tbody>
<tr>
<td>Common-Mode Rejection Ratio</td>
<td>$V_S = \pm 18V$</td>
<td>(V–) + 2</td>
<td>(V+) – 1.4</td>
<td>V</td>
</tr>
</tbody>
</table>

### Input Impedance

| COMMON-MODE | Differential | $20k || 8$ | Ω || pF |
|-------------|--------------|-------------|--------|
|             | Common-Mode  | $10^3 || 2$ | Ω || pF |

### Open-Loop Gain

<table>
<thead>
<tr>
<th>OPEN-LOOP VOLTAGE GAIN</th>
<th>$A_{OL}(V–) + 0.2V \leq V_O \leq (V+) – 0.2V$, $R_L = 10kΩ$</th>
<th>114</th>
<th>130</th>
<th>dB</th>
</tr>
</thead>
<tbody>
<tr>
<td>Over Temperature</td>
<td>$A_{OL}(V–) + 0.6V \leq V_O \leq (V+) – 0.6V$, $R_L = 600Ω$</td>
<td>110</td>
<td>114</td>
<td>dB</td>
</tr>
</tbody>
</table>

### Frequency Response

<table>
<thead>
<tr>
<th>FREQUENCY RESPONSE</th>
<th>GBW $G = 100$</th>
<th>80</th>
<th>MHz</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>$G = 1$</td>
<td>45</td>
<td>MHz</td>
</tr>
<tr>
<td>Slew Rate</td>
<td>$SR = 27$</td>
<td>ns</td>
<td>V/μs</td>
</tr>
<tr>
<td>Setting Time, 0.01%</td>
<td>$t_s = 100$</td>
<td>ns</td>
<td>ns</td>
</tr>
<tr>
<td>0.0015% (16-bit)</td>
<td>$t_s = 100$</td>
<td>ns</td>
<td>ns</td>
</tr>
<tr>
<td>Overload Recovery Time</td>
<td>$G = –10$</td>
<td>ns</td>
<td>ns</td>
</tr>
<tr>
<td>Total Harmonic Distortion + Noise</td>
<td>THD+N $G = +1$, $I = 1kHz$, $V_O = 3V_{RMS}$, $R_L = 600Ω$</td>
<td>0.000015</td>
<td>%</td>
</tr>
</tbody>
</table>

(1) The OPA2211-HT is not intended to be used as a comparator due to its limited differential input range capability. Refer to the INPUT PROTECTION section of this data sheet.
ELECTRICAL CHARACTERISTICS: $V_S = \pm 2.25\text{V}$ to $\pm 18\text{V}$ (continued)

BOLDFACE limits apply over the specified temperature range, $T_J = -55^\circ\text{C}$ to $+150^\circ\text{C}$.

At $T_J = +25^\circ\text{C}$, $R_L = 10\text{k}\Omega$ connected to midsupply, $V_{CM} = V_{OUT} = \text{midsupply}$, unless otherwise noted.

<table>
<thead>
<tr>
<th>PARAMETER</th>
<th>CONDITIONS</th>
<th>Standard Grade OPA2211</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
<td>MIN</td>
</tr>
<tr>
<td>Output Voltage</td>
<td>$V_{OUT}$</td>
<td></td>
</tr>
<tr>
<td></td>
<td>$R_L = 10\text{k}\Omega$, $A_{CL} \geq 114\text{dB}$</td>
<td>(V–) + 0.2</td>
</tr>
<tr>
<td></td>
<td>$R_L = 60\text{Ω}$, $A_{CL} \geq 110\text{dB}$</td>
<td>(V–) + 0.6</td>
</tr>
<tr>
<td></td>
<td>$I_C &lt; 15\text{mA}$, $A_{CL} \geq 100\text{dB}$</td>
<td>(V–) + 0.6</td>
</tr>
<tr>
<td>Short-Circuit Current</td>
<td>$I_{SC}$</td>
<td></td>
</tr>
<tr>
<td>Capacitive Load Drive</td>
<td>$C_{LOAD}$</td>
<td>See Typical Characteristics</td>
</tr>
<tr>
<td>Open-Loop Output Impedance</td>
<td>$Z_O$</td>
<td>5</td>
</tr>
<tr>
<td></td>
<td>$f = 1\text{MHz}$</td>
<td></td>
</tr>
<tr>
<td>Power Supply</td>
<td>$V_S$</td>
<td>±2.25</td>
</tr>
<tr>
<td>Quiescent Current</td>
<td>$I_Q$</td>
<td>3.6</td>
</tr>
<tr>
<td>(per channel)</td>
<td>$I_{OUT} = 0\text{A}$</td>
<td></td>
</tr>
<tr>
<td>Over Temperature</td>
<td>$T_A$</td>
<td>–55</td>
</tr>
<tr>
<td>Temperature Range</td>
<td>$T_A$</td>
<td>–55</td>
</tr>
</tbody>
</table>

(1) See Datasheet for Absolute Maximum and Minimum Recommended Operating Conditions.
(2) Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).
(3) The predicted operating lifetime vs. junction temperature is based on reliability modeling and available qualification data.
(4) Device is qualified for 1000 hour operation at 150°C. Device is functional at 175°C, but at reduced operating life.

Figure 1. OPA2211-HT Wirebond Life Derating Chart
TYPICAL CHARACTERISTICS
At $T_A = +25^\circ C$, $V_S = \pm 18V$, and $R_L = 10k\Omega$, unless otherwise noted.

INPUT VOLTAGE NOISE DENSITY vs FREQUENCY

INPUT CURRENT NOISE DENSITY vs FREQUENCY

THD+N RATIO vs FREQUENCY

THD+N RATIO vs OUTPUT VOLTAGE AMPLITUDE

0.1Hz TO 10Hz NOISE
TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ \text{C}$, $V_S = \pm 18\text{V}$, and $R_L = 10\text{k}\Omega$, unless otherwise noted.

POWER-SUPPLY REJECTION RATIO vs FREQUENCY (Referred to Input)

COMMON-MODE REJECTION RATIO vs FREQUENCY

OPEN-LOOP OUTPUT IMPEDANCE vs FREQUENCY

GAIN AND PHASE vs FREQUENCY

OPEN-LOOP GAIN vs TEMPERATURE

Figure 7.

Figure 8.

Figure 9.

Figure 10.

Figure 11.
TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ C$, $V_S = \pm 18V$, and $R_L = 10k\Omega$, unless otherwise noted.

OFFSET VOLTAGE PRODUCTION DISTRIBUTION

OFFSET VOLTAGE DRIFT PRODUCTION DISTRIBUTION

$I_B$ AND $I_{OS}$ CURRENT vs TEMPERATURE

OFFSET VOLTAGE vs COMMON-MODE VOLTAGE

$V_{OS}$ WARMUP

INPUT OFFSET CURRENT vs SUPPLY VOLTAGE

Figure 12.

Figure 13.

Figure 14.

Figure 15.

Figure 16.

Figure 17.
TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ$C, $V_S = \pm 18$V, and $R_L = 10\,\Omega$, unless otherwise noted.

**INPUT OFFSET CURRENT vs COMMON-MODE VOLTAGE**

$V_S = 36$V

3 Typical Units Shown

Common-Mode Range

$V_{CM}$ (V)

Figure 18.

**INPUT BIAS CURRENT vs COMMON-MODE VOLTAGE**

$V_S = 36$V

3 Typical Units Shown

$I_B$ (nA)

Unit 1

Unit 2

Unit 3

Common-Mode Range

$V_{CM}$ (V)

Figure 20.

**QUIESCENT CURRENT vs TEMPERATURE**

$I_Q$ (mA)

Temperature (°C)

Figure 21.

**QUIESCENT CURRENT vs SUPPLY VOLTAGE**

$I_Q$ (mA)

$V_S$ (V)

Figure 22.

**NORMALIZED QUIESCENT CURRENT vs TIME**

$I_{Q_{Shift}}$ (mA)

Time (s)

Figure 23.

Average of 10 Typical Units
TYPICAL CHARACTERISTICS (continued)

At $T_A = +25°C$, $V_S = ±18V$, and $R_L = 10kΩ$, unless otherwise noted.

**SHORT-CIRCUIT CURRENT vs TEMPERATURE**

![Short-Circuit Current vs Temperature Graph](image)

**SMALL,SIGNAL STEP RESPONSE (100mV)**

![Small-Signal Step Response Graph](image)

**SMALL-SIGNAL STEP RESPONSE vs CAPACITIVE LOAD (100mV Output Step)**

![Small-Signal Step Response vs Capacitive Load Graph](image)
TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ C$, $V_S = \pm 18V$, and $R_L = 10k\Omega$, unless otherwise noted.

### LARGE-SIGNAL STEP RESPONSE

- **Figure 30.**

### LARGE-SIGNAL POSITIVE SETTLING TIME

- **10V<sub>pp</sub>, $C_L = 100pF$**

- **Figure 32.**

### LARGE-SIGNAL NEGATIVE SETTLING TIME

- **10V<sub>pp</sub>, $C_L = 100pF$**

- **Figure 34.**

### LARGE-SIGNAL STEP RESPONSE

- **Figure 31.**

- **$R_f = 1000\Omega$**

Note: See the Applications Information section, Input Protection.
TYPICAL CHARACTERISTICS (continued)

At $T_A = +25^\circ C$, $V_S = \pm 18V$, and $R_L = 10k\Omega$, unless otherwise noted.

NEGATIVE OVERLOAD RECOVERY

POSITIVE OVERLOAD RECOVERY

OUTPUT VOLTAGE vs OUTPUT CURRENT

NO PHASE REVERSAL

Figure 36.

Figure 37.

Figure 38.

Figure 39.
APPLICATION INFORMATION

The OPA2211 is a unity-gain stable, precision op amp with very low noise. Applications with noisy or high-impedance power supplies require decoupling capacitors close to the device pins. In most cases, 0.1\(\mu\)F capacitors are adequate. Figure 40 shows a simplified schematic of the OPA2211. This die uses a SiGe bipolar process and contains 180 transistors.

OPERATING VOLTAGE

OPA2211 series op amps operate from ±2.25V to ±18V supplies while maintaining excellent performance. The OPA2211 series can operate with as little as +4.5V between the supplies and with up to +36V between the supplies. However, some applications do not require equal positive and negative output voltage swing. With the OPA2211 series, power-supply voltages do not need to be equal. For example, the positive supply could be set to +25V with the negative supply at –5V or vice-versa.

The common-mode voltage must be maintained within the specified range. In addition, key parameters are assured over the specified temperature range, \(T_J = –55^\circ C\) to +150\(^\circ\)C. Parameters that vary significantly with operating voltage or temperature are shown in the Typical Characteristics.

Figure 40. OPA2211 Simplified Schematic
INPUT PROTECTION

The input terminals of the OPA2211 are protected from excessive differential voltage with back-to-back diodes, as shown in Figure 41. In most circuit applications, the input protection circuitry has no consequence. However, in low-gain or G = 1 circuits, fast ramping input signals can forward bias these diodes because the output of the amplifier cannot respond rapidly enough to the input ramp. This effect is illustrated in Figure 31 of the Typical Characteristics. If the input signal is fast enough to create this forward bias condition, the input signal current must be limited to 10mA or less. If the input signal current is not inherently limited, an input series resistor can be used to limit the signal input current. This input series resistor degrades the low-noise performance of the OPA2211, and is discussed in the Noise Performance section of this data sheet. Figure 41 shows an example implementing a current-limiting feedback resistor.

![Figure 41. Pulsed Operation](image)

NOISE PERFORMANCE

Figure 42 shows total circuit noise for varying source impedances with the op amp in a unity-gain configuration (no feedback resistor network, and therefore no additional noise contributions). Two different op amps are shown with total circuit noise calculated. The OPA2211 has very low voltage noise, making it ideal for low source impedances (less than 2kΩ). A similar precision op amp, the OPA227, has somewhat higher voltage noise but lower current noise. It provides excellent noise performance at moderate source impedance (10kΩ to 100kΩ). Above 100kΩ, a FET-input op amp such as the OPA132 (very low current noise) may provide improved performance. The equation in Figure 42 is shown for the calculation of the total circuit noise. Note that $e_v =$ voltage noise, $I_n =$ current noise, $R_s =$ source impedance, $k =$ Boltzmann’s constant $= 1.38 \times 10^{-23}$ J/K, and $T$ is temperature in K.

![Figure 42. Noise Performance of the OPA2211 and OPA227 in Unity-Gain Buffer Configuration](image)

BASIC NOISE CALCULATIONS

Design of low-noise op amp circuits requires careful consideration of a variety of possible noise contributors: noise from the signal source, noise generated in the op amp, and noise from the feedback network resistors. The total noise of the circuit is the root-sum-square combination of all noise components.

The resistive portion of the source impedance produces thermal noise proportional to the square root of the resistance. This function is plotted in Figure 41. Pulsed Operation Figure 42 shows total noise for varying source impedances with the op amp in a unity-gain configuration (no feedback resistor network, and therefore no additional noise contributions). The operational amplifier itself contributes both a voltage noise component and a current noise component.

The voltage noise is commonly modeled as a time-varying component of the offset voltage. The current noise may dominate. The operational amplifier itself contributes both a voltage noise component and a current noise component.
illustrates both inverting and noninverting op amp circuit configurations with gain. In circuit configurations with gain, the feedback network resistors also contribute noise. The current noise of the op amp reacts with the feedback resistors to create additional noise components. The feedback resistor values can generally be chosen to make these noise sources negligible. The equations for total noise are shown for both configurations.

**TOTAL HARMONIC DISTORTION MEASUREMENTS**

OPA2211 series op amps have excellent distortion characteristics. THD + Noise is below 0.0001% \((G = +1, V_O = 3V_{RMS})\) throughout the audio frequency range, 20Hz to 20kHz, with a 600Ω load.

The distortion produced by OPA2211 series op amps is below the measurement limit of many commercially available distortion analyzers. However, a special test circuit illustrated in can be used to extend the measurement capabilities.

**ELECTRICAL OVERSTRESS**

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but may involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

It is helpful to have a good understanding of this basic ESD circuitry and its relevance to an electrical overstress event. Figure 43 illustrates the ESD circuits contained in the OPA2211 (indicated by the dashed line area). The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power-supply lines, where they meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

Op amp distortion can be considered an internal error source that can be referred to the input. shows a circuit that causes the op amp distortion to be 101 times greater than that normally produced by the op amp. The addition of \(R_3\) to the otherwise standard noninverting amplifier configuration alters the feedback factor or noise gain of the circuit. The closed-loop gain is unchanged, but the feedback available for error correction is reduced by a factor of 101, thus extending the resolution by 101. Note that the input signal and load applied to the op amp are the same as with conventional feedback without \(R_3\). The value of \(R_3\) should be kept small to minimize its effect on the distortion measurements.

Validity of this technique can be verified by duplicating measurements at high gain and/or high frequency where the distortion is within the measurement capability of the test equipment. Measurements for this data sheet were made with an Audio Precision System Two distortion/noise analyzer, which greatly simplifies such repetitive measurements. The measurement technique can, however, be performed with manual distortion measurement instruments.

An ESD event produces a short duration, high-voltage pulse that is transformed into a short duration, high-current pulse as it discharges through a semiconductor device. The ESD protection circuits are designed to provide a current path around the operational amplifier core to prevent it from being damaged. The energy absorbed by the protection circuitry is then dissipated as heat.

When an ESD voltage develops across two or more of the amplifier device pins, current flows through one or more of the steering diodes. Depending on the path that the current takes, the absorption device may activate. The absorption device has a trigger, or threshold voltage, that is above the normal operating voltage of the OPA2211 but below the device breakdown voltage level. Once this threshold is exceeded, the absorption device quickly activates and clamps the voltage across the supply rails to a safe level.

When the operational amplifier connects into a circuit such as that illustrated in Figure 43, the ESD protection components are intended to remain inactive and not become involved in the application circuit operation. However, circumstances may arise where an applied voltage exceeds the operating voltage range of a given pin. Should this condition occur, there is a risk that some of the internal ESD protection circuits may be biased on, and conduct current. Any such current flow occurs through steering diode paths and rarely involves the absorption device.
Figure 43 depicts a specific example where the input voltage, $V_{\text{IN}}$, exceeds the positive supply voltage ($+V_S$) by 500mV or more. Much of what happens in the circuit depends on the supply characteristics. If $+V_S$ can sink the current, one of the upper input steering diodes conducts and directs current to $+V_S$. Excessively high current levels can flow with increasingly higher $V_{\text{IN}}$. As a result, the datasheet specifications recommend that applications limit the input current to 10mA.

If the supply is not capable of sinking the current, $V_{\text{IN}}$ may begin sourcing current to the operational amplifier, and then take over as the source of positive supply voltage. The danger in this case is that the voltage can rise to levels that exceed the operational amplifier absolute maximum ratings. In extreme but rare cases, the absorption device triggers on while $+V_S$ and $-V_S$ are applied. If this event happens, a direct current path is established between the $+V_S$ and $-V_S$ supplies. The power dissipation of the absorption device is quickly exceeded, and the extreme internal heating destroys the operational amplifier.

Another common question involves what happens to the amplifier if an input signal is applied to the input while the power supplies $+V_S$ and/or $-V_S$ are at 0V. Again, it depends on the supply characteristic while at 0V, or at a level below the input signal amplitude. If the supplies appear as high impedance, then the operational amplifier supply current may be supplied by the input source via the current steering diodes. This state is not a normal bias condition; the amplifier most likely will not operate normally. If the supplies are low impedance, then the current through the steering diodes can become quite high. The current level depends on the ability of the input source to deliver current, and any resistance in the input path.
### Packaging Information

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<td>-55 to 150</td>
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</table>

(1) The marketing status values are defined as follows:
- **ACTIVE**: Product device recommended for new designs.
- **LIFEBUY**: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
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NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <http://www.ti.com>.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. Falls within JEDEC MO-153.

PowerPAD is a trademark of Texas Instruments.
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For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

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NOTE:  A. All linear dimensions are in millimeters

Exposed tie strap features may not be present.
NOTES:  
A. All linear dimensions are in millimeters.  
B. This drawing is subject to change without notice.  
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.  
D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com (http://www.ti.com). Publication IPC-7351 is recommended for alternate designs.  
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.  
F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.
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